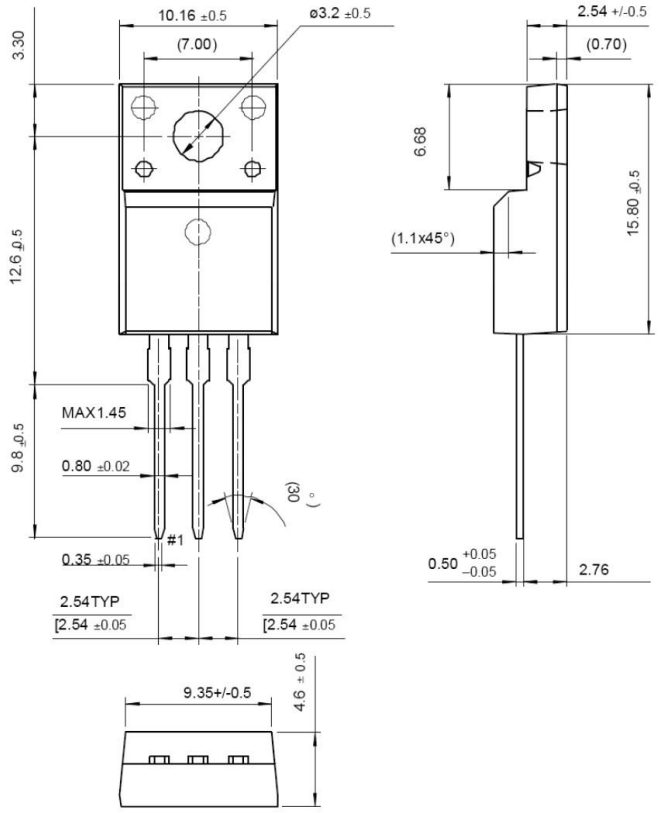
MS49N60

N-Channel 40V MOSFETs

Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.



Features

- 40V,150A, RDS(ON) =3.8mΩ@VGS = 10V
- Improved dv/dt capability
- Fast switching
- Green Device Available
- RoHS compliant package

Applications

- MB / VGA / Vcore
- POL Applications
- SMPS 2nd SR

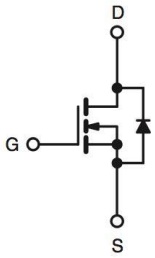
Package type：TO-220

Packing & Order Information

3.000/Box

RoHS
MPLIANT

Graphic symbol



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current - Continuous (T_C=25°C) (Chip Limitation)	150	A
	Drain Current - Continuous (T_C=100°C) (Chip Limitation)	83	A
I_{DM}	Drain Current - Pulsed[1]	400	A
EAS	Single Pulse Avalanche Energy[2]	312	mJ

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Absolute Maximum Ratings (T_A=25°C unless otherwise noted)			
Symbol	**Parameter**	**Value**	**Unit**
IAS	Single Pulse Avalanched Current[2]	79	A
P_D	Power Dissipation (T_C=25°C)	135	W
	Power Dissipation - Derate above 25°C	1.08	W/°C
T_J	Operating Junction Temperature Range	-55 to +150	°C
T_{STG}	Storage Temperature Range	-55 to +150	°C

Thermal Characteristics				
Symbol	**Parameter**	**Typ.**	**Max.**	**Units**
$R_{\Theta jA}$	Thermal Resistance Junction to ambient	--	62	°C/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	--	0.92	

Electrical Characteristics (TJ=25℃, unless otherwise noted)

Off Characteristics						
Symbol	**Parameter**	**Test Conditions**	**Min**	**Typ.**	**Max.**	**Units**
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = V_{GS}, I_D = 250uA	40			V
ΔBV_{DSS} /ΔTJ	BVDSS Temperature Coefficient	Reference to 25°C , ID=1mA		0.03		V/°C
I_{GSS}	Gate-Source Leakage Current	V_{DS} = 0 V , V_{GS} = ±20 V			±100	nA
I_{DSS}	Drain-Source Leakage Current	V_{DS} = 40 V , V_{GS} = 0 V , T_J= 25°C V_{DS} = 32 V , V_{GS} = 0 V , T_J= 125°C			1 10	uA

On Characteristics						
Symbol	**Parameter**	**Test Conditions**	**Min**	**Typ.**	**Max.**	**Units**
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 25 A V_{GS} = 4.5 V , I_D = 12 A		3.1 4.0	3.8 5.0	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D =-250μA	1.2	1.6	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient	V_{DS} = V_{GS}, I_D =-250μA		-5		mV/°C
g_{fs}	Forward Tranconductance	V_{DS} = 10 V , I_D = 2 A		45		S

Dynamic and switching Characteristics						
Symbol	**Parameter**	**Test Conditions**	**Min**	**Typ.**	**Max.**	**Units**
$t_{d(on)}$	Turn-On Delay Time[3,4]	I_D = 1 A , R_G = 6 Ω, V_{GS} = 10 V , V_{DD} = 20 V	--	28	50	ns
t_r	Rise Time[3,4]		--	3.2	6.5	ns
$t_{d(off)}$	Turn-Off Delay Time[3,4]		--	89	160	ns
tf	Fall Time[3,4]		--	14	28	ns

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Dynamic and switching Characteristics						
Symbol	**Parameter**	**Test Conditions**	**Min**	**Typ.**	**Max.**	**Units**
Q_g	Total Gate Charge[3,4]	V_{DS} = 20 V , I_D = 10 A, V_{GS} = 4.5 V	--	44.4	80	nC
Q_{gs}	Gate-Source Charge[3,4]		--	9.6	18	nC
Q_{gd}	Gate-Drain Charge[3,4]		--	16	30	nC
C_{ISS}	Input Capacitance	V_{DS} = 25 V f = 1 MHz , V_{GS} = 0 V	--	4940	7800	pF
C_{OSS}	Output Capacitance		--	425	800	pF
C_{RSS}	Reverse Transfer Capacitance		--	170	330	pF
Rg	Total Gate Charge	V_{DS} = 0 V , f = 1 MHz , V_{GS} = 0 V	--	1.4	2.8	Ω

Drain-Source Diode Characteristics and Maximum Ratings						
Symbol	**Parameter**	**Test Conditions**	**Min**	**Typ.**	**Max.**	**Units**
I_S	Continuous Source Current	V_G = V_D = 0 V , Force Current	--	--	100	A
I_{SM}	Pulsed Source Current		--	--	200	A
V_{SD}	Diode Forward Voltage	V_{GS} = 0 V , I_S = 1 A , TJ = 25°C	--	--	1	V

Note :

1.Repetitive Rating : Pulsed width limited by maximum junction temperature.

2. VDD=25V,VGS=10V,L=0.1mH,IAS=79A., Starting TJ=25℃

3.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.

4.Essentially independent of operating temperature.

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■Characteristics Curve

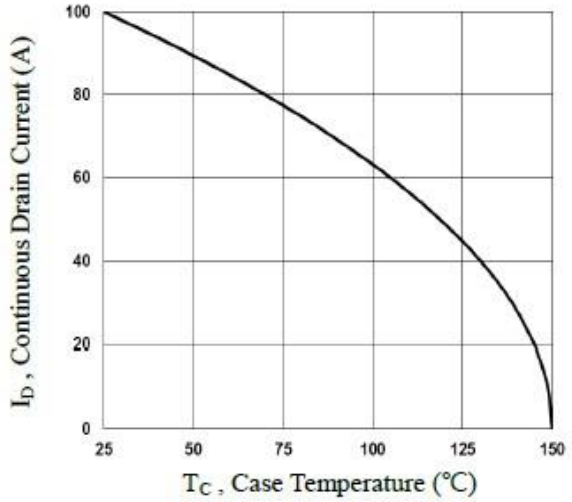

FIG.1-CONTINUOUS DRAIN CURRENT VS. TC

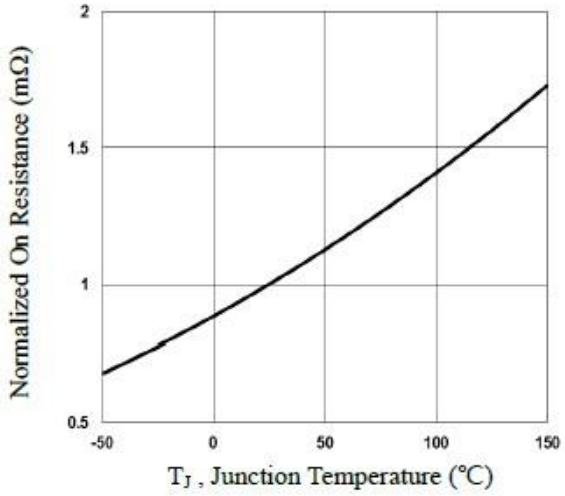

FIG.2-NORMALIZED RDSON VS. TJ

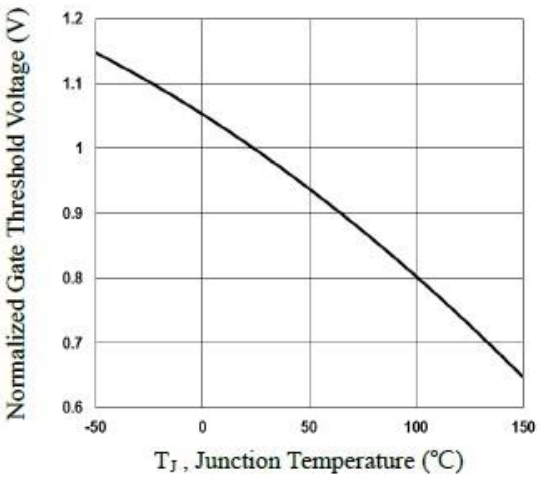

FIG.3-NORMALIZED VTH VS. TJ

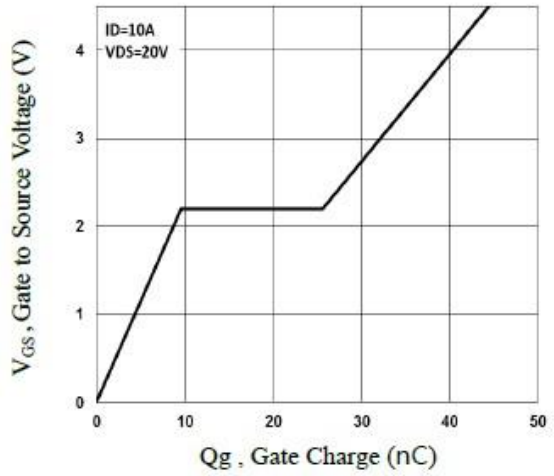

FIG.4-GATE CHARGE WAVEFORM

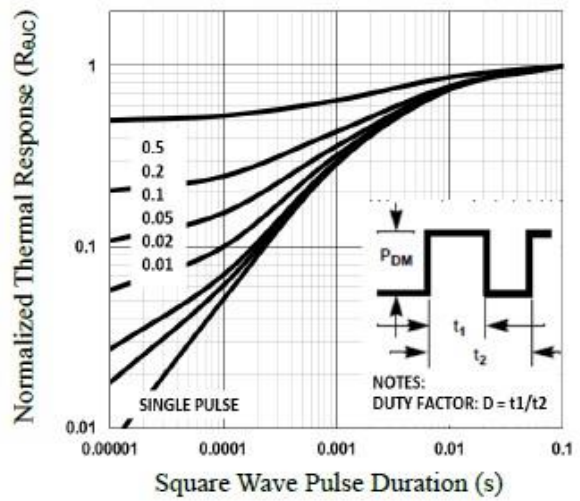

FIG.5-NORMALIZED TRANSIENT IMPEDANCE

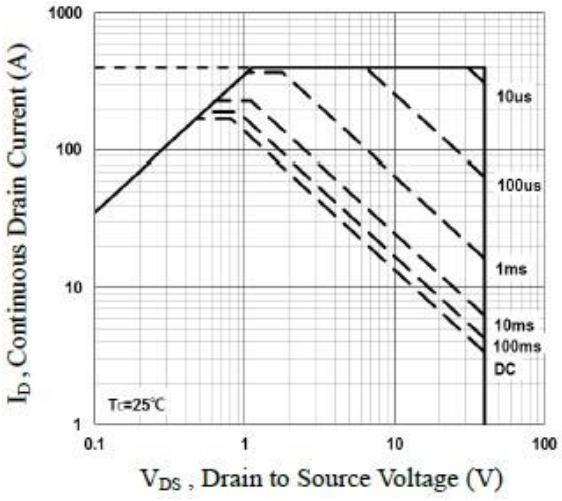

FIG.6-MAXIMUM SAFE OPERATION AREA

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■Characteristics Curve

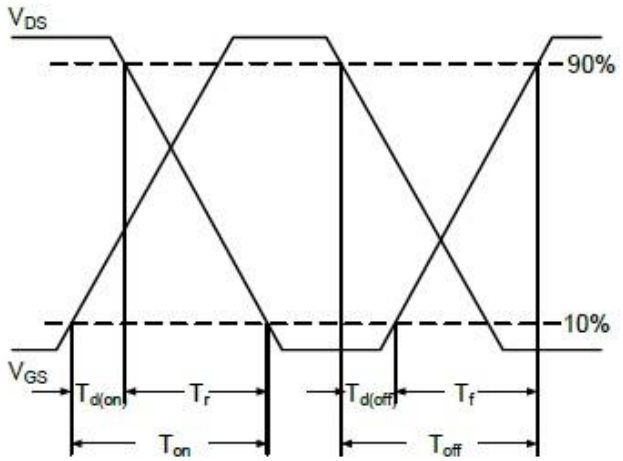

FIG.7-SWITCHING TIME WAVEFORM

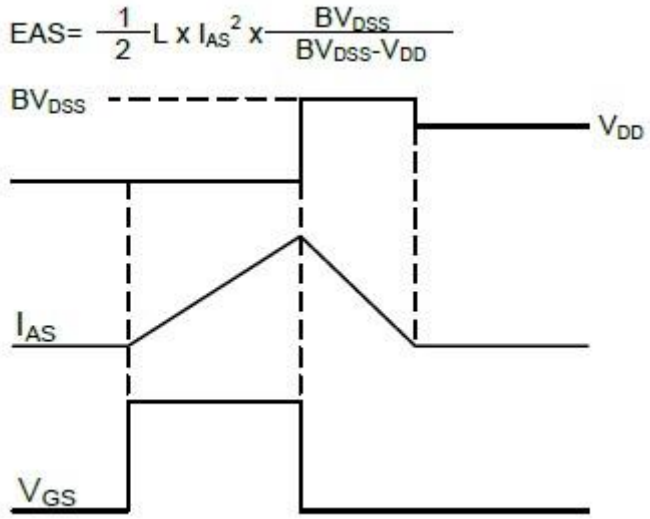

FIG.8-EAS WAVEFORM

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